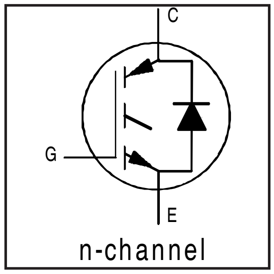
International
IOR Rectifier

PD- 95189

IRG4PH50KDPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE

Short Circuit Rated
UltraFast IGBT



V_{CES} = 1200V

$V_{CE(on)\ typ.}$ = 2.77V

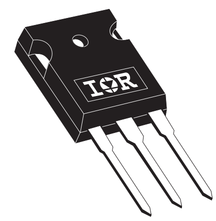
@V_{GE} = 15V, I_C = 24A

Features

- High short circuit rating optimized for motor control, t_{sc} =10µs, V_{CC} = 720V , T_J = 125°C, V_{GE} = 15V
- Combines low conduction losses with high switching speed
- Tighter parameter distribution and higher efficiency than previous generations
- IGBT co-packaged with HEXFRED^{TM} ultrafast, ultrasoft recovery antiparallel diodes
- Lead-Free

Benefits

- Latest generation 4 IGBT's offer highest power density motor controls possible
- HEXFRED^{TM} diodes optimized for performance with IGBTs. Minimized recovery characteristics reduce noise, EMI and switching losses
- This part replaces the IRGPH50KD2 and IRGPH50MD2 products
- For hints see design tip 97003



TO-247AC

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
I_C @ T_C = 25°C	Continuous Collector Current	45	A
I_C @ T_C = 100°C	Continuous Collector Current	24	
I_{CM}	Pulsed Collector Current ①	90	
I_{LM}	Clamped Inductive Load Current ②	90	
I_F @ T_C = 100°C	Diode Continuous Forward Current	16	
I_{FM}	Diode Maximum Forward Current	90	
t_{sc}	Short Circuit Withstand Time	10	µs
V_{GE}	Gate-to-Emitter Voltage	± 20	V
P_D @ T_C = 25°C	Maximum Power Dissipation	200	W
P_D @ T_C = 100°C	Maximum Power Dissipation	78	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	–––	–––	0.64	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode	–––	–––	0.83	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	–––	0.24	–––	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	–––	–––	40	
Wt	Weight	–––	6 (0.21)	–––	g (oz)

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage③	1200	—	—	V	V_{GE} = 0V, I_C = 250μA	
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.91	—	V/°C	V_{GE} = 0V, I_C = 1.0mA	
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.77	3.5	V	I_C = 24A	V_{GE} = 15V
		—	3.28	—		I_C = 45A	See Fig. 2, 5
		—	2.54	—		I_C = 24A, T_J = 150°C	
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}$, I_C = 250μA	
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-10	—	mV/°C	$V_{CE} = V_{GE}$, I_C = 250μA	
g_{fe}	Forward Transconductance ④	13	19	—	S	V_{CE} = 100V, I_C = 24A	
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	V_{GE} = 0V, V_{CE} = 1200V	
		—	—	6500		V_{GE} = 0V, V_{CE} = 1200V, T_J = 150°C	
V_{FM}	Diode Forward Voltage Drop	—	2.5	3.5	V	I_C = 16A	See Fig. 13
		—	2.1	3.0		I_C = 16A, T_J = 150°C	
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±20V	

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions		
Q_g	Total Gate Charge (turn-on)	—	180	270	nC	I_C = 24A		
Q_{ge}	Gate - Emitter Charge (turn-on)	—	25	38		V_{CC} = 400V	See Fig.8	
Q_{gc}	Gate - Collector Charge (turn-on)	—	70	110		V_{GE} = 15V		
$t_{d(on)}$	Turn-On Delay Time	—	87	—	ns			
t_r	Rise Time	—	100	—		T_J = 25°C		
$t_{d(off)}$	Turn-Off Delay Time	—	140	300		I_C = 24A, V_{CC} = 800V		
t_f	Fall Time	—	200	300		V_{GE} = 15V, R_G = 5.0Ω		
E_{on}	Turn-On Switching Loss	—	3.83	—	mJ	Energy losses include "tail"		
E_{off}	Turn-Off Switching Loss	—	1.90	—		and diode reverse recovery		
E_{ts}	Total Switching Loss	—	5.73	7.9		See Fig. 9,10,18		
t_{sc}	Short Circuit Withstand Time	10	—	—	μs	V_{CC} = 720V, T_J = 125°C		
						V_{GE} = 15V, R_G = 5.0Ω		
$t_{d(on)}$	Turn-On Delay Time	—	67	—	ns	T_J = 150°C,	See Fig. 10,11,18	
t_r	Rise Time	—	72	—		I_C = 24A, V_{CC} = 800V		
$t_{d(off)}$	Turn-Off Delay Time	—	310	—		V_{GE} = 15V, R_G = 5.0Ω,		
t_f	Fall Time	—	390	—		Energy losses include "tail"		
E_{ts}	Total Switching Loss	—	8.36	—	mJ	and diode reverse recovery		
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package		
C_{ies}	Input Capacitance	—	2800	—	pF	V_{GE} = 0V		
C_{oes}	Output Capacitance	—	140	—		V_{CC} = 30V	See Fig. 7	
C_{res}	Reverse Transfer Capacitance	—	53	—		f = 1.0MHz		
t_{rr}	Diode Reverse Recovery Time	—	90	135	ns	T_J = 25°C	See Fig.	
		—	164	245		T_J = 125°C	14	I_F = 16A
I_{rr}	Diode Peak Reverse Recovery Current	—	5.8	10	A	T_J = 25°C	See Fig.	
		—	8.3	15		T_J = 125°C	15	V_R = 200V
Q_{rr}	Diode Reverse Recovery Charge	—	260	675	nC	T_J = 25°C	See Fig.	
		—	680	1838		T_J = 125°C	16	di/dt = 200A/μs
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery	—	120	—	A/μs	T_J = 25°C	See Fig.	
	During t_b	—	76	—		T_J = 125°C	17	

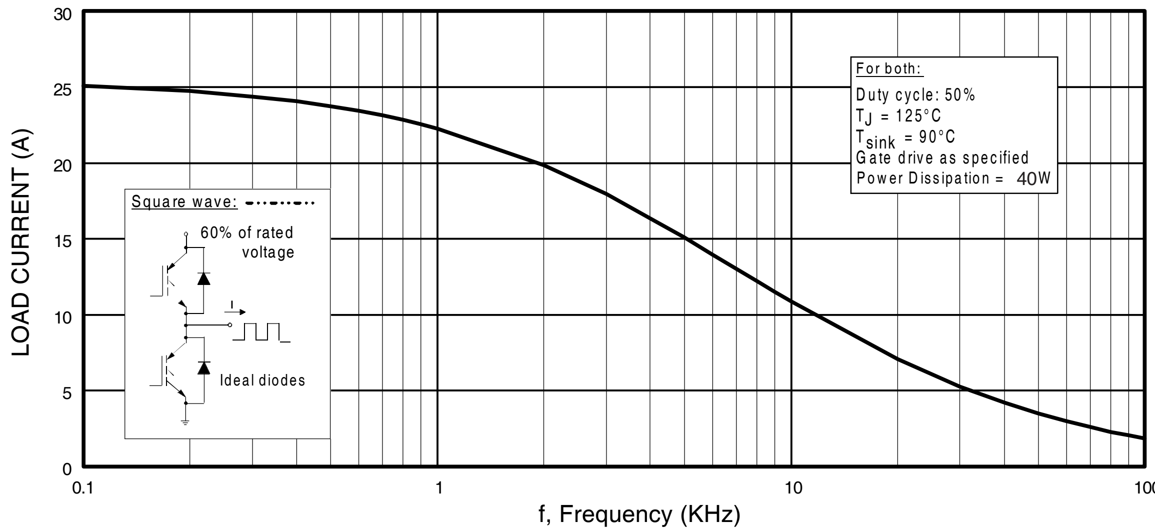


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

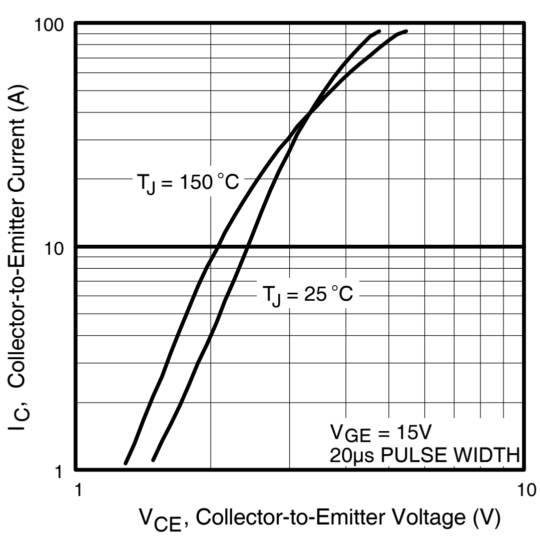


Fig. 2 - Typical Output Characteristics

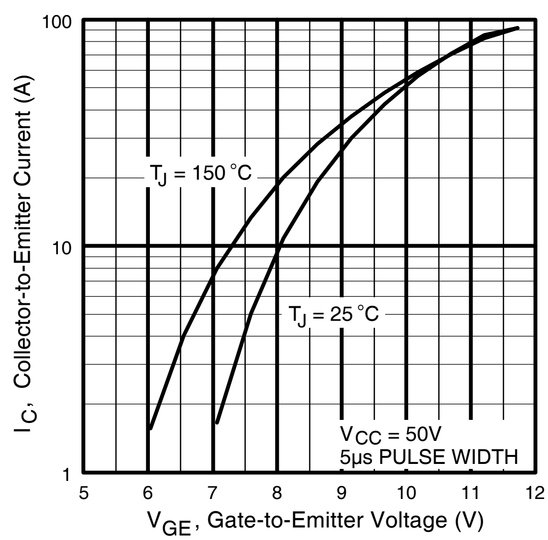


Fig. 3 - Typical Transfer Characteristics

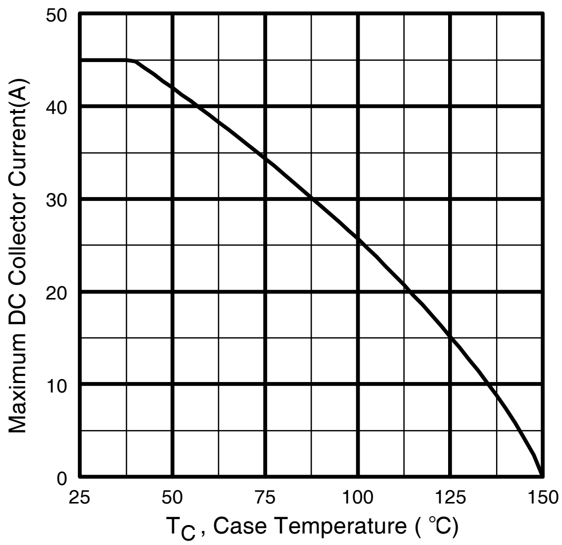


Fig. 4 - Maximum Collector Current vs. Case Temperature

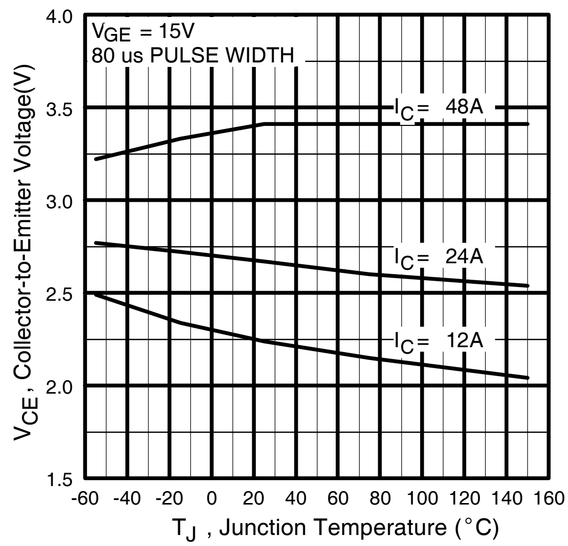


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

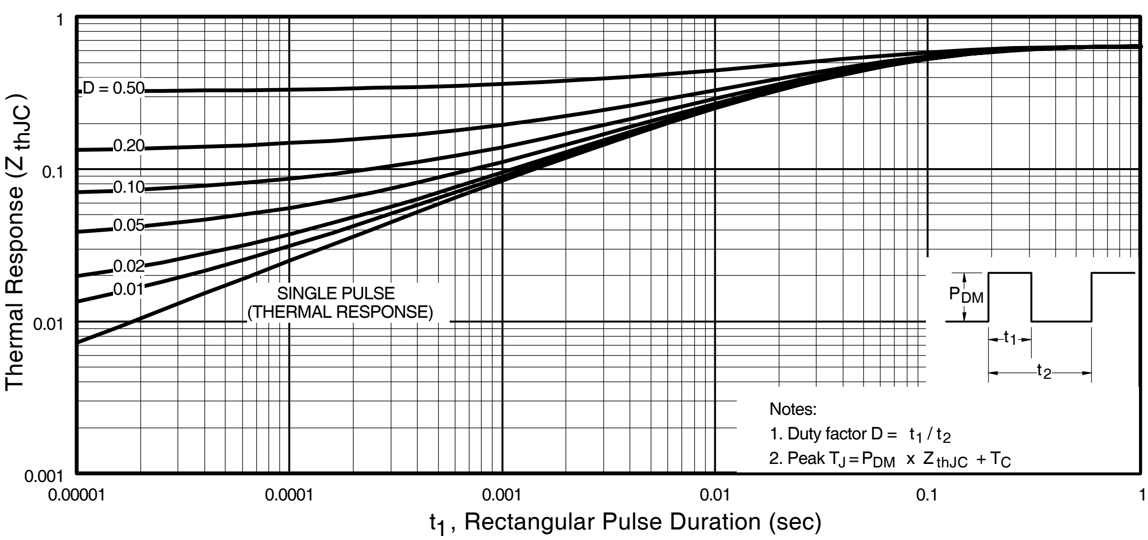


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

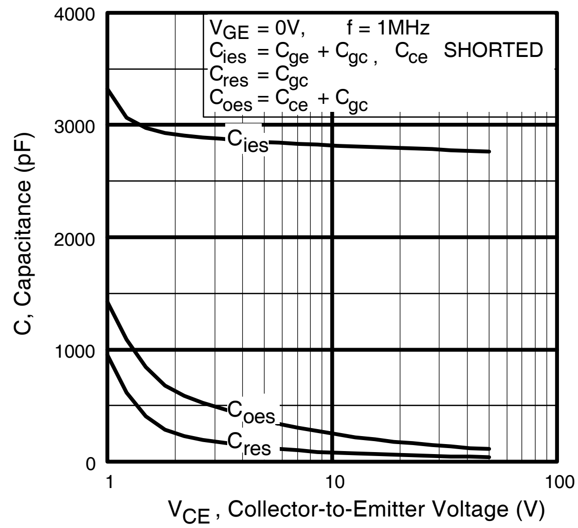


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

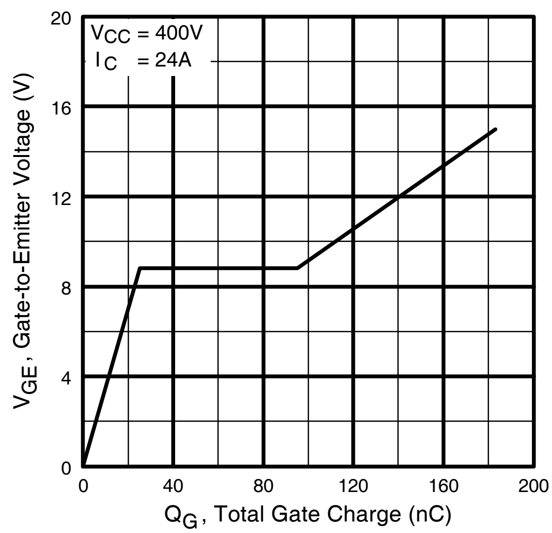


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

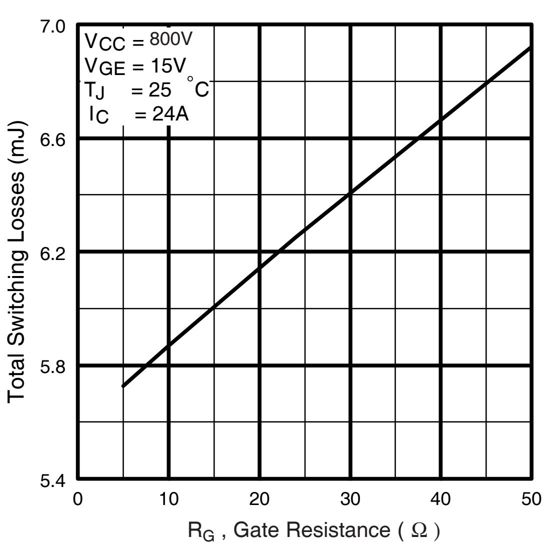


Fig. 9 - Typical Switching Losses vs. Gate Resistance

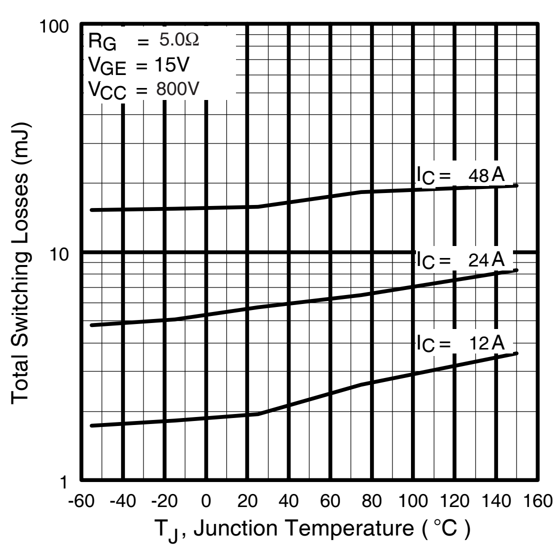


Fig. 10 - Typical Switching Losses vs. Junction Temperature

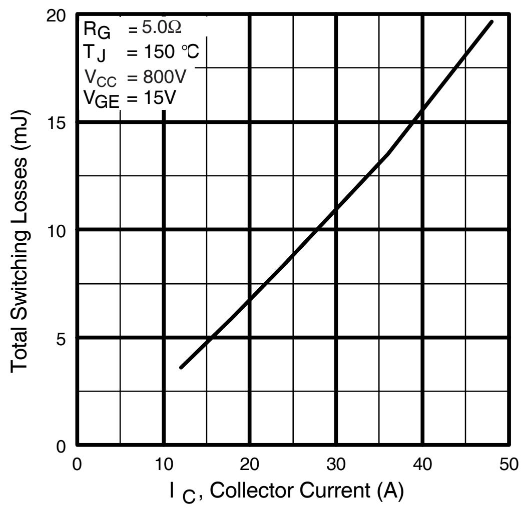


Fig. 11 - Typical Switching Losses vs. Collector Current

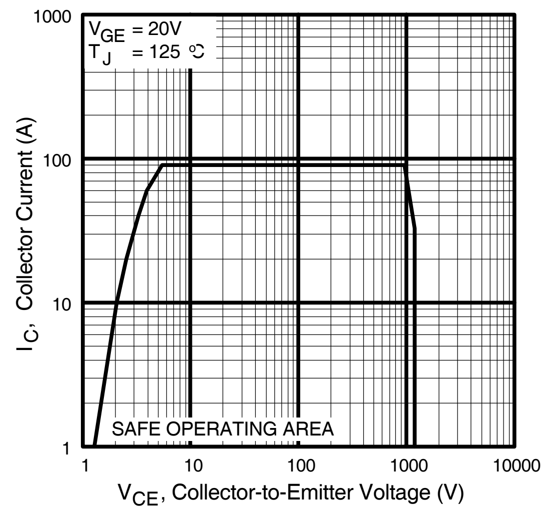


Fig. 12 - Turn-Off SOA

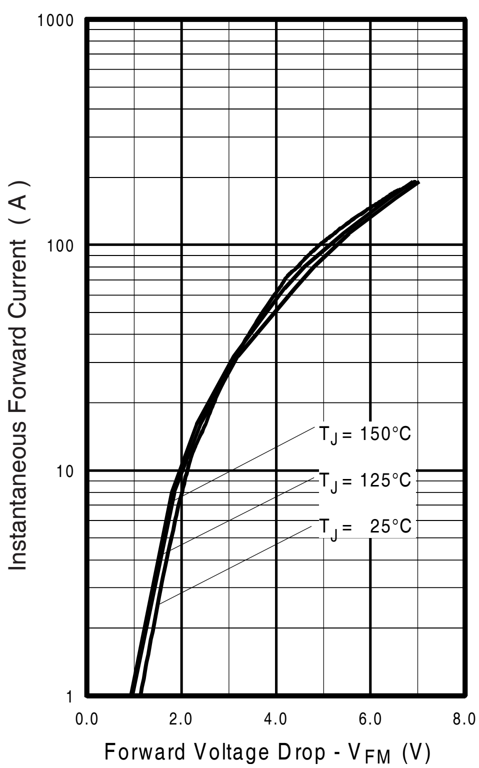


Fig. 13 - Typical Forward Voltage Drop vs. Instantaneous Forward Current

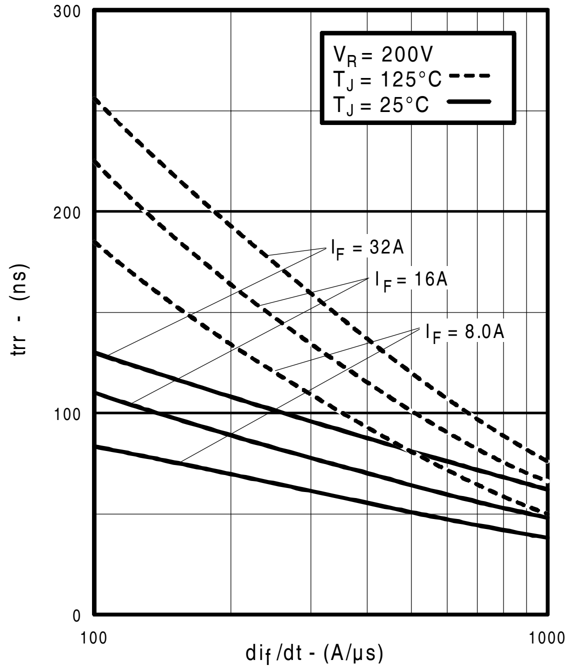


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

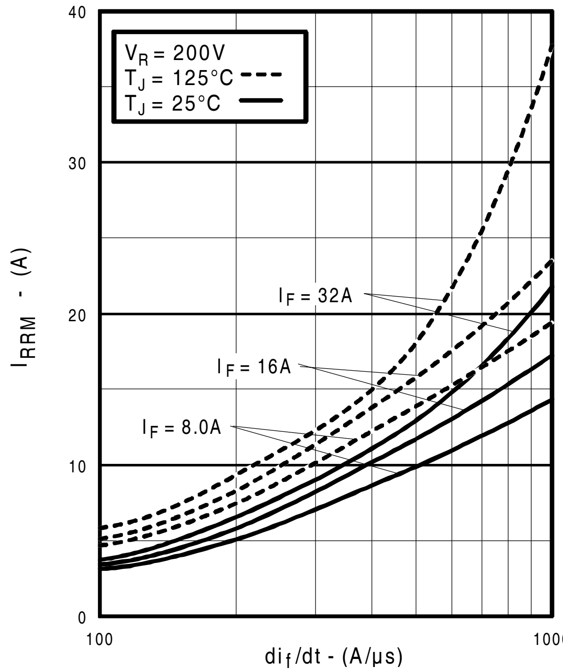


Fig. 15 - Typical Recovery Current vs. di_f/dt

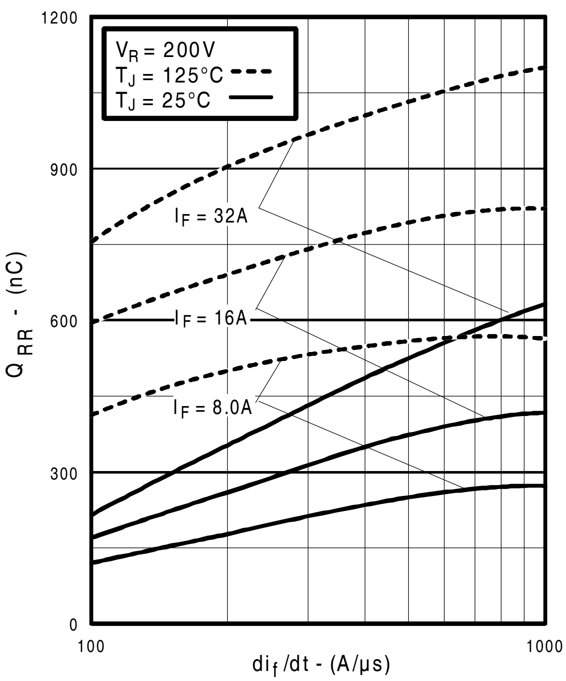


Fig. 16 - Typical Stored Charge vs. di_f/dt

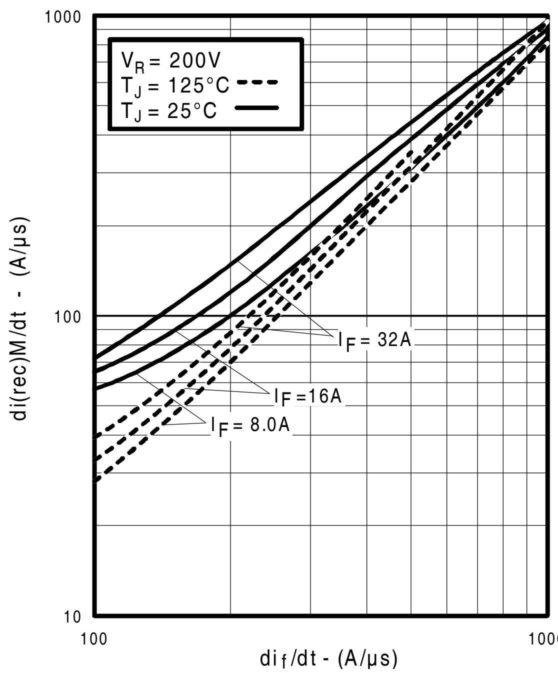


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

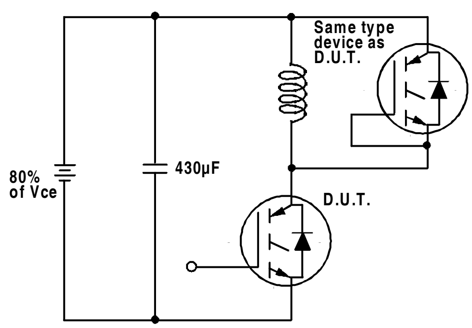


Fig. 18a - Test Circuit for Measurement of I_{LM}, E_{on}, $E_{off(diode)}$, t_{rr}, Q_{rr}, I_{rr}, $t_{d(on)}$, t_r, $t_{d(off)}$, t_f

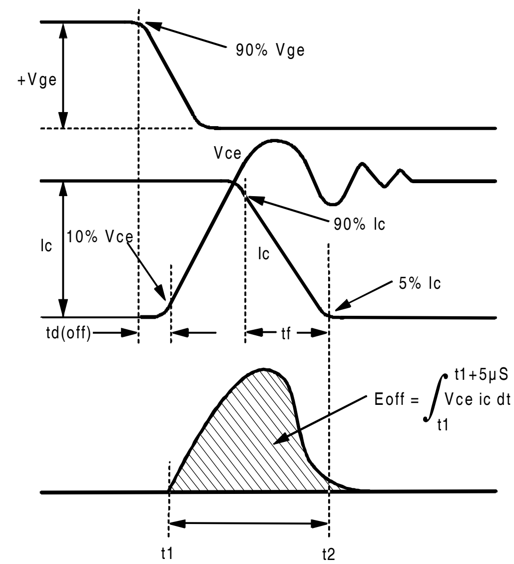


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off}, $t_{d(off)}$, t_f

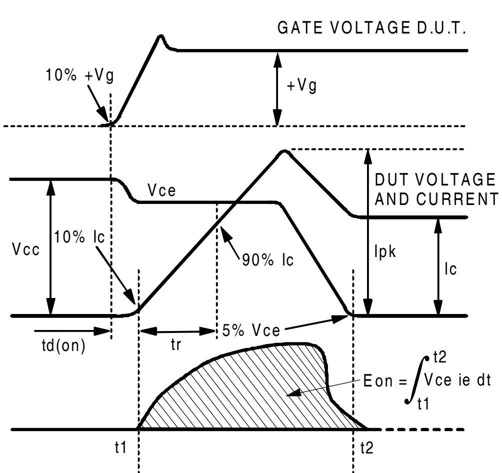


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on}, $t_{d(on)}$, t_r

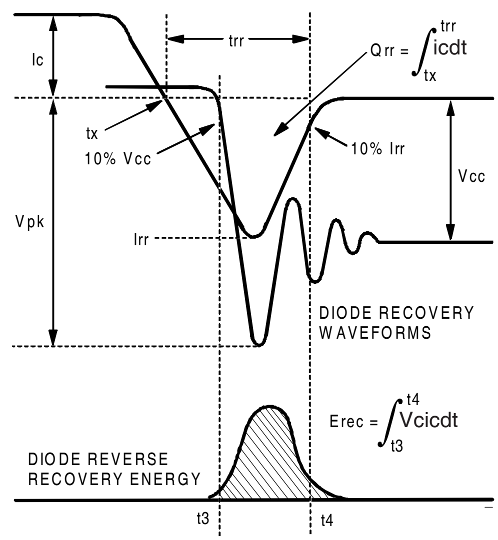


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec}, t_{rr}, Q_{rr}, I_{rr}

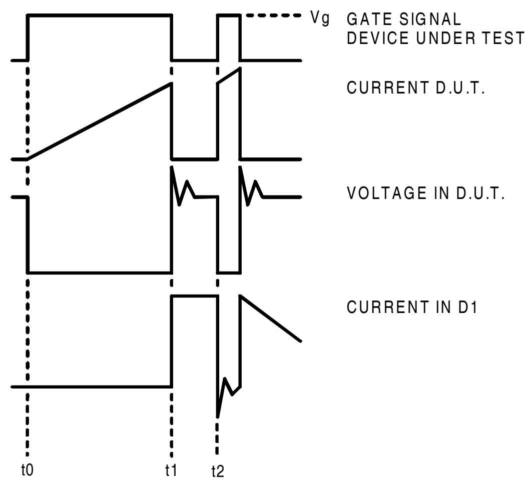


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

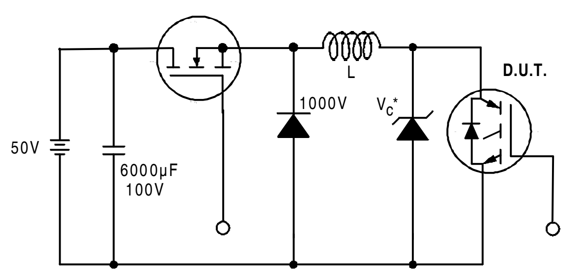


Figure 19. Clamped Inductive Load Test Circuit

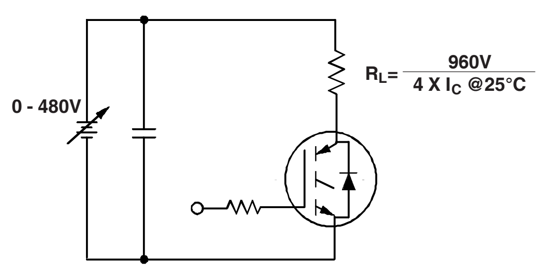


Figure 20. Pulsed Collector Current Test Circuit

Notes:

① Repetitive rating: V_{GE}=20V; pulse width limited by maximum junction temperature (figure 20)

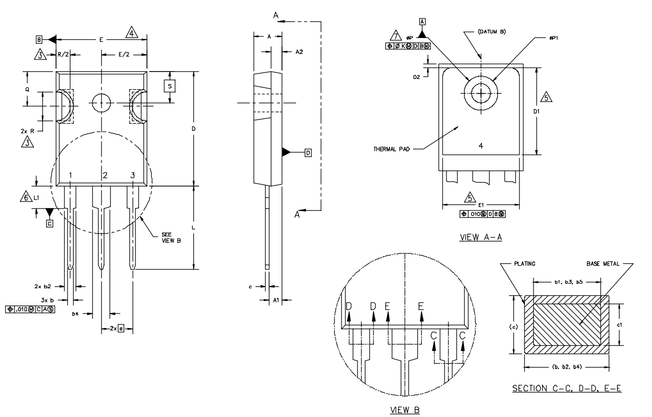
② V_{CC}=80%(V_{CES}), V_{GE}=20V, L=10µH, R_G= 5.0Ω (figure 19)

③ Pulse width ≤ 80µs; duty factor ≤ 0.1%.

④ Pulse width 5.0µs, single shot.

TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENISONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. øP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154" [3.91].
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247 WITH THE EXCEPTION OF DIMENSION c.

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.37	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.034	0.38	0.86	
c1	.015	.030	0.38	0.76	
D	.776	.815	19.71	20.70	4
D1	.515	–	13.08	–	5
D2	.020	.030	0.51	0.76	
E	.602	.625	15.29	15.87	4
E1	.540	–	15.72	–	
e	.215 BSC		5.46 BSC		
Øk	.010		2.54		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
N	3		7.62 BSC		
øP	.140	.144	3.56	3.66	
øP1	–	.275	–	6.98	
Q	.209	.224	5.31	5.69	
R	.178	.216	4.52	5.49	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

1.– GATE
2.– DRAIN
3 – SOURCE
4.– DRAIN

IGBTs, CoPACK

1 – GATE
2.– COLLECTOR
3.– EMITTER
4.– COLLECTOR

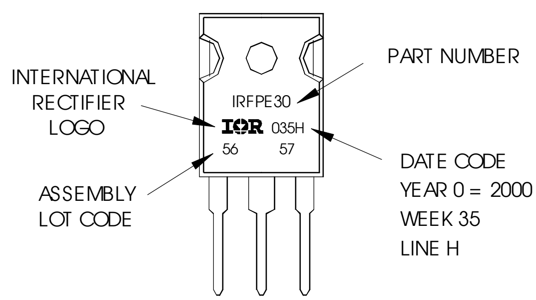
DIODES

1.– ANODE/OPEN
2 – CATHODE
3.– ANODE

TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2000
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.

International
IOR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903
Visit us at www.irf.com for sales contact information. 04/04

Note: For the most current drawings please refer to the IR website at:
http://www.irf.com/package/